The synthesis of CuxS from Cu layers by low pressure plasma processing supplementary data

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Raman spectra of CuxS layers grown under the conditions in table 1:

|  |  |
| --- | --- |
| Parameter | Value |
| MW power (W) | 800 |
| Magnet Current (A) | 5 |
| Process time (min) | 10, 30, 60 |
| SF6 flow rate (m3/s) | 3.33x10-7 |
| Process pressure (Pa) | 1.33 |
| Temperature (K) | 373, 473, 523, 573, 623, 673 |

Raman spectra of samples grown at 623 K for 30 minutes:





Raman spectra of samples grown at 573 K for 10 minutes:







Raman spectra of samples grown at 573 K for 30 minutes:







Raman spectra of samples grown at 573 K for 60 minutes:





Raman spectra of samples grown at 523 K for 60 minutes:







Raman spectra of samples grown at 473 K for 60 minutes:





